APPLICATION DATA SHEET

Electronic Version v14

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Title of Invention

METHOD FOR FABRICATING A SEMICONDUCTOR TRANSISTOR DEVICE HAVING ULTRA-SHALLOW SOURCE/DRAIN EXTENSIONS

Application Type : regular, utility
Attorney Docket Number : NAUP0591USA

Correspondence address:

Customer Number: 027765

Inventors Information:

Inventor 1:

Applicant Authority Type: Inventor **Citizenship:** TW

Given Name: Yun-Ren Family Name: Wang

Residence:

City of Residence: Tai-Nan City

Country of Residence: TW

Address-1 of Mailing Address: 2F-15, No. 128, Gongyuan Rd., North District

Address-2 of Mailing Address:

City of Mailing Address: Tai-Nan City

State of Mailing Address:

Postal Code of Mailing Address:

Country of Mailing Address: TW

Phone: Fax:

E-mail:

Inventor 2:

Applicant Authority Type: Inventor **Citizenship:** TW

Given Name: Ying-Wei Family Name: Yen

Residence:

City of Residence: Miao- Li Hsien

Country of Residence: TW

Address-1 of Mailing Address: No. 159, Chongshan Rd., Tongxiao

Address-2 of Mailing Address:

City of Mailing Address: Miao- Li Hsien

State of Mailing Address:

Postal Code of Mailing Address:

Country of Mailing Address: TW

Phone:

Fax: E-mail:

Inventor 3:

Applicant Authority Type: Inventor **Citizenship:** TW

Given Name: Shu-Yen Family Name: Chan

Residence:

City of Residence: Hsin-Chu Hsien

Country of Residence: TW

Address-1 of Mailing Address: 5F-2, No. 42, Guohua St., Chubei

Address-2 of Mailing Address:

City of Mailing Address: Hsin-Chu Hsien

State of Mailing Address:

Postal Code of Mailing Address:

Country of Mailing Address: TW

Phone: Fax:

E-mail:

Attorney Information:

practitioner(s) at Customer Number:

027765



as our attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.